REMARKS

The specification has been amended to correct minor informalities therein.

Examination on the merits is requested.

Respectfully submitted,

Eric J. Robinson
Registration No. 38,285

NIXON PEABODY LLP
8180 Greensboro Drive, Suite 800
McLean, Virginia 22102
(703) 790-9110

N183028.1

VERSION WITH MARKINGS TO SHOW CHANGES MADE

Please amend the specification starting at page 17, line 23 through page 18, line 2 as follows:

Next, sputtering is carried out in a sputtering system having a chamber kept at a vacuum of 1 x 10[^{5}]$^{-5}$ through 1 x 10[^{7}] $^{-7}$ Pa, so as to deposit a metal film, such as a cobalt film 110, on the entire surface of the semiconductor substrate 100 as is shown in FIG. 3(c).

Please amend the specification starting at page 28, line 21 through page 29, line 8 as follows:

Next, as is shown in FIG. 79a), after removing the silicon oxide film 209, the sputtering is carried out in a sputtering system having a chamber kept at a degree of vacuum of 1 x 10[^{5}] $^{-5}$ through 1 x 10[^{7}] $^{-7}$ Pa, thereby depositing a metal film, such as a cobalt film 211, on the entire surface of the semiconductor substrate 200. In this manner, similarly to Embodiment 2, cobalt atoms included in the cobalt film 211 are incorporated into the crystal lattice of silicon. Therefore, a nucleus of cobalt disilicide ($CoSi_2$) is formed on the interface between the n-type high concentration impurity layer 208 and the cobalt film 210, and a nucleus of cobalt disilicide ($CoSi_2$) is formed with respect to each crystal grain of the gate electrode 205.